

V1.1 Datasheet

N-Channel 30V MOSFET

FEATURES

- ●Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

PRODUCTY SUMMARY				
V _{DS}	R _{DS(}	_{on)} m(Ω) Max		
30	12	@V _{GS} =10V		
30	16	@V _{GS} =4.5V		

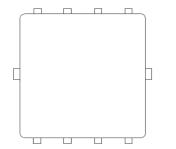
Application

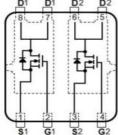
- Portable Devices
- ■Consumer Electronics

Mechanical

■Case:DFN3333 Package

DFN3333





Packing Information

Package	Packing	
DFN3333	5Kpcs/13"Reel	

Maximum Ratings (T _A =25°C unless otherwise specified)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	30	V			
Gate-Source Voltage	V _{GS}	±20	V			
Continuous Drain Current 1)	I _D	20	А			
Continuous Drain Current 4)	I _{DM}	80	W			
Maximum Power Dissipation	P _D	5	А			
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C			

Typical Thermal Res	sistance		
Parameter	Symbol	Limit	Unit
Junction-to-Ambient Thermal Resistance 3)	$R_{\theta JA}$	34	°C/W

Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Fused current that based on wire numbers and diameter.
- Guaranteed by design, not subject to production testing.
- 4. The maximum current rating is package limited.
- 5. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keepinitial $T_J = 25$ °C.

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Electrical Characteristics (T _A = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Symbol	Test Condition	Limits			l Init
			Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	B _{VDSS}	V _{GS} =0V, I _D =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.38	3.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =10V, I_D =20A	ı	10	12	mΩ
		V_{GS} =4.5V, I_D =17A	-	14	16	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V			1	uA
GateSource Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V			±100	nA

DrainSource Diode						
Maximum Continuous Body Diode Forward Current	I _S	-	-	-	1.2	А
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V	-	-	1.5	V

Note:

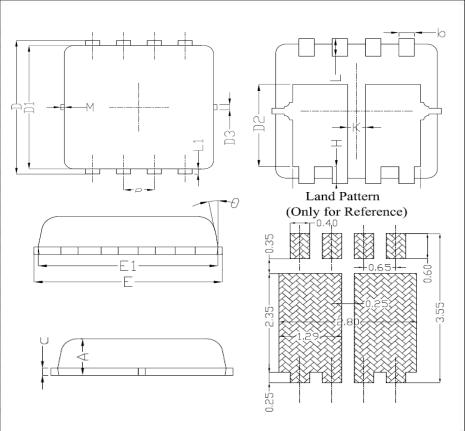
- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

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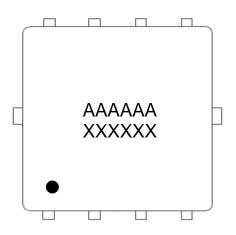


Package Outline Dimensions (inches and millimeters)

	DF	N333	33			
	Dimensions					
SYMBOL	Millin	neters	Inches			
	Min	Max	Min	Max		
Α	0.70	0.80	0.03	0.03		
b	0.25	0.35	0.01	0.01		
С	0.10	0.25	0.00	0.01		
D	3.25	3.45	0.13	0.14		
D1	3.00	3.20	0.12	0.13		
D2	1.78	1.98	0.07	0.08		
D3	<u>-</u>	0.13	150	0.01		
E	3.20	3.40	0.13	0.13		
E1	3.00	3.20	0.12	0.13		
E2	2.39	2.59	0.09	0.10		
е		0.65	BSC	5)		
Н	0.30	0.50	0.01	0.02		
L	0.30	0.50	0.01	0.02		
L1	0.13		- 0.00			
K	0.30	72	0.01			
θ	-	12	8=0	12		
M		0.15	8 .4 0	0.01		



Marking Information



AAAAAA = Product number

XXXXXX = Tracking number

Third line = Pin1 Point

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